

### N-Channel Super Junction Power MOSFET III

### **General Description**

The series of devices use advanced trench gate super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

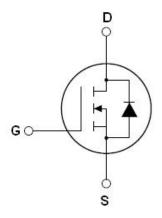
#### **Features**

- New technology for high voltage device
- Low on-resistance and low conduction losses
- small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

### **Application**

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

| V <sub>DS</sub>        | 650  | V  |
|------------------------|------|----|
| R <sub>DS(ON)TYP</sub> | 290  | mΩ |
| $I_D$                  | 11.5 | A  |



Schematic diagram

### **Package Marking And Ordering Information**

| Device     | Device Package | Marking    |
|------------|----------------|------------|
| NCE65T360D | TO-263         | NCE65T360D |
| NCE65T360  | TO-220         | NCE65T360  |
| NCE65T360F | TO-220F        | NCE65T360F |







**TO-263** 

**TO-220** 

**TO-220F** 

v1.1

Table 1. Absolute Maximum Ratings (T<sub>c</sub>=25℃)

| Parameter   | Symbol                  | NCE65T360D<br>NCE65T360 | NCE65T360F | Unit |
|---|-------------------------|-------------------------|------------|------|
| Drain-Source Voltage (Vgs=0V)   | VDS                     | 65                      | 50         | V    |
| Gate-Source Voltage (V <sub>DS</sub> =0V), AC(f>1HZ)                  | V <sub>G</sub> s        | 土                       | 30         | V    |
| Continuous Drain Current at T <sub>C</sub> =25°C                      | I <sub>D (DC)</sub>     | 11.5                    | 11.5*      | А    |
| Continuous Drain Current at T <sub>C</sub> =100°C                     | I <sub>D (DC)</sub>     | 7                       | 7*         | Α    |
| Pulsed drain current (Note 1)   | I <sub>DM (pluse)</sub> | 46                      | 46*        | Α    |
| Maximum Power Dissipation(T <sub>C</sub> =25 ℃)                       | P <sub>D</sub>          | 101                     | 32.6       | W    |
| Derate above 25°C   |                         | 0.81                    | 0.26       | W/°C |
| Single pulse avalanche energy (Note2)                                 | Eas                     | 144                     |            | mJ   |
| Avalanche current <sup>(Note 1)</sup>                                 | I <sub>AR</sub>         | 6                       |            | А    |
| Repetitive Avalanche energy , $t_{AR}$ limited by $T_{jmax}$ (Note 1) | E <sub>AR</sub>         | 0                       | .5         | mJ   |



| Parameter  | Symbol           | NCE65T360D<br>NCE65T360 | NCE65T360F | Unit |
|--|------------------|-------------------------|------------|------|
| Drain Source voltage slope, V <sub>DS</sub> ≤480 V,                          | dv/dt            | 50                      |            | V/ns |
| Reverse diode dv/dt, V <sub>DS</sub> ≤480 V,I <sub>SD</sub> <i<sub>D</i<sub> | dv/dt            | 15                      |            | V/ns |
| Operating Junction and Storage Temperature Range                             | $T_{J}, T_{STG}$ | -55                     | +150       | °C   |

<sup>\*</sup> limited by maximum junction temperature

#### **Table 2. Thermal Characteristic**

| Parameter   | Symbol            | NCE65T360D<br>NCE65T360 | NCE65T360F | Unit  |
|---|-------------------|-------------------------|------------|-------|
| Thermal Resistance, Junction-to-Case (Maximum)    | R <sub>thJC</sub> | 1.24                    | 3.83       | °C /W |
| Thermal Resistance, Junction-to-Ambient (Maximum) | R <sub>thJA</sub> | 62                      | 80         | °C /W |

 Table 3. Electrical Characteristics (TA=25<sup>o</sup>Cunless otherwise noted)

| Parameter                                | Symbol              | Condition   | Min | Тур  | Max  | Unit |
|--|---------------------|---|-----|------|------|------|
| On/off states                            |                     |   |     |      | •    | •    |
| Drain-Source Breakdown Voltage           | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250μA               | 650 |      |      | V    |
| Zero Gate Voltage Drain Current(Tc=25℃)  | I <sub>DSS</sub>    | V <sub>DS</sub> =650V,V <sub>GS</sub> =0V               |     | 0.05 | 1    | μA   |
| Zero Gate Voltage Drain Current(Tc=125℃) | I <sub>DSS</sub>    | V <sub>DS</sub> =650V,V <sub>GS</sub> =0V               |     |      | 100  | μA   |
| Gate-Body Leakage Current                | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V               |     |      | ±100 | nA   |
| Gate Threshold Voltage                   | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA | 3   | 3.5  | 4    | V    |
| Drain-Source On-State Resistance         | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =7A                |     | 290  | 360  | mΩ   |
| Dynamic Characteristics                  |                     |   |     |      |      |      |
| Input Capacitance                        | C <sub>lss</sub>    | \/ -50\/\/ -0\/   |     | 870  |      | pF   |
| Output Capacitance                       | Coss                | $V_{DS}$ =50V, $V_{GS}$ =0V,<br>F=1.0MHz                |     | 54   |      | pF   |
| Reverse Transfer Capacitance             | C <sub>rss</sub>    | F-1.UIVITZ  |     | 1.8  |      | pF   |
| Total Gate Charge                        | Qg                  | V 400V/1 44.5A  |     | 19   |      | nC   |
| Gate-Source Charge                       | Q <sub>gs</sub>     | V <sub>DS</sub> =480V,I <sub>D</sub> =11.5A,            |     | 6    |      | nC   |
| Gate-Drain Charge                        | $Q_{gd}$            | V <sub>GS</sub> =10V                                    |     | 6.5  |      | nC   |
| Switching times                          |                     |   |     |      | •    | •    |
| Turn-on Delay Time                       | t <sub>d(on)</sub>  |   |     | 11   |      | nS   |
| Turn-on Rise Time                        | t <sub>r</sub>      | V <sub>DD</sub> =380V,I <sub>D</sub> =5.5A,             |     | 8    |      | nS   |
| Turn-Off Delay Time                      | t <sub>d(off)</sub> | $R_G=3\Omega,V_{GS}=10V$                                |     | 58   | 70   | nS   |
| Turn-Off Fall Time                       | t <sub>f</sub>      |   |     | 9    | 14   | nS   |
| Source- Drain Diode Characteristics      |                     |   |     |      |      |      |
| Source-drain current(Body Diode)         | I <sub>SD</sub>     | T -05°C   |     |      | 11.5 | Α    |
| Pulsed Source-drain current(Body Diode)  | I <sub>SDM</sub>    | T <sub>C</sub> =25°C                                    |     |      | 46   | Α    |
| Forward on voltage                       | V <sub>SD</sub>     | Tj=25°C,I <sub>SD</sub> =11.5A,V <sub>GS</sub> =0V      |     | 0.9  | 1.2  | V    |
| Reverse Recovery Time                    | t <sub>rr</sub>     | T: 05°0 L 5 0A  |     | 220  |      | nS   |
| Reverse Recovery Charge                  | Qrr                 | Tj=25°C,I <sub>F</sub> =5.8A,                           |     | 2.2  |      | uC   |
| Peak Reverse Recovery Current            | Irrm                | di/dt=100A/μs   |     | 19   |      | Α    |

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25  $^{\circ}\text{C}$  ,VDD=50V,VG=10V, R<sub>G</sub>=25 $\Omega$ 



### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure 1. Safe operating area

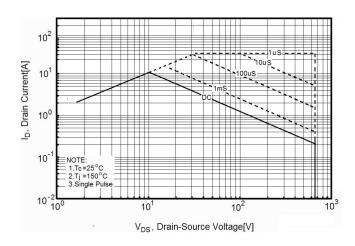


Figure 2. Safe operating area for TO-220F

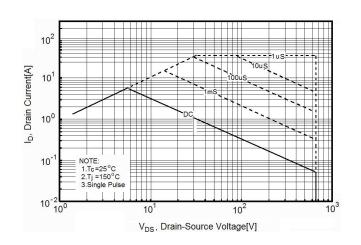


Figure 3. Source-Drain Diode Forward Voltage

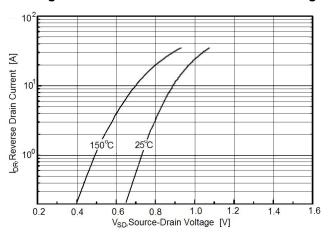


Figure 4. Output characteristics

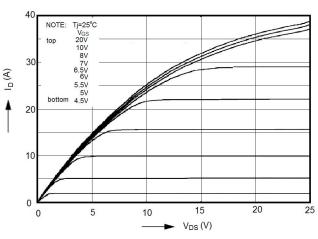


Figure 5. Transfer characteristics

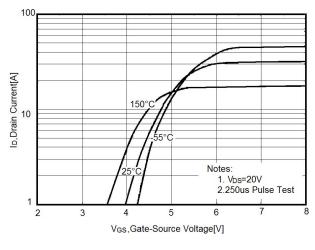


Figure 6. Static drain-source on resistance

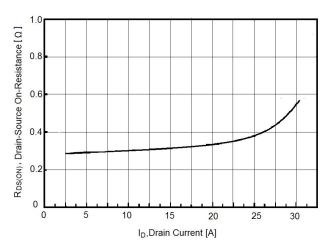




Figure 7. R<sub>DS(ON)</sub> vs Junction Temperature

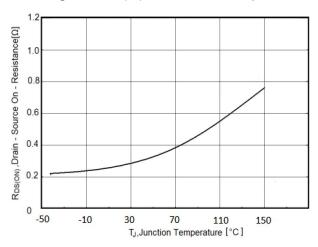


Figure 8. BV<sub>DSS</sub> vs Junction Temperature

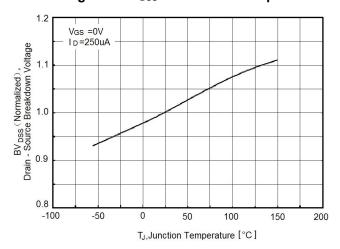


Figure 9. Maximum ID vs Junction Temperature

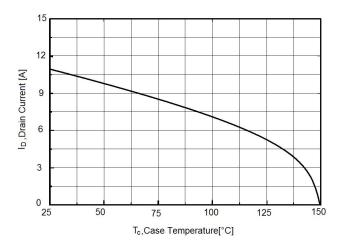


Figure 10. Gate charge waveforms

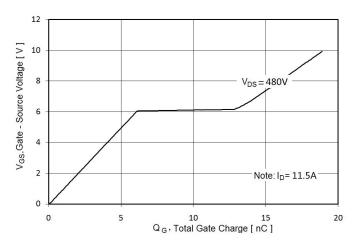


Figure 11. Capacitance

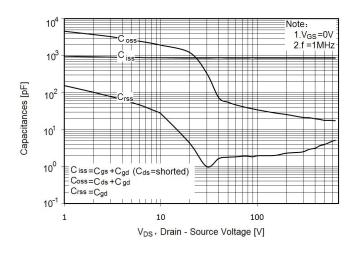


Figure 12. Transient Thermal Impedance

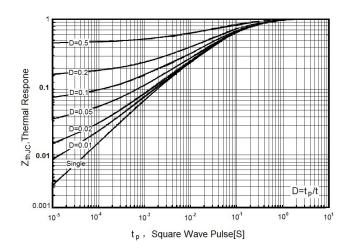
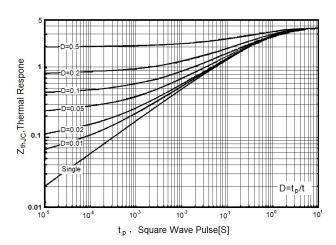




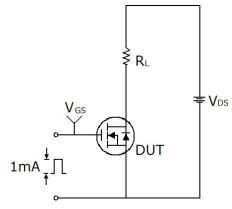
Figure 13. Transient Thermal Impedance for TO-220F

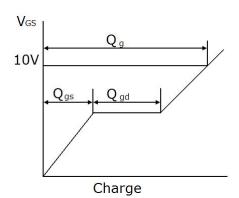




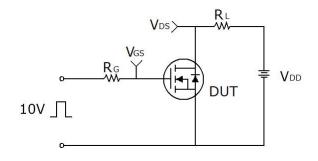
### **Test circuit**

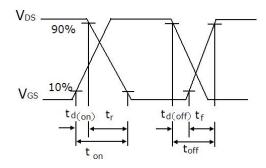
### 1) Gate charge test circuit & Waveform



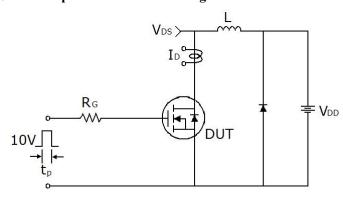


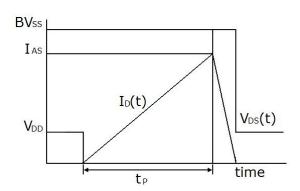
### 2) Switch Time Test Circuit:





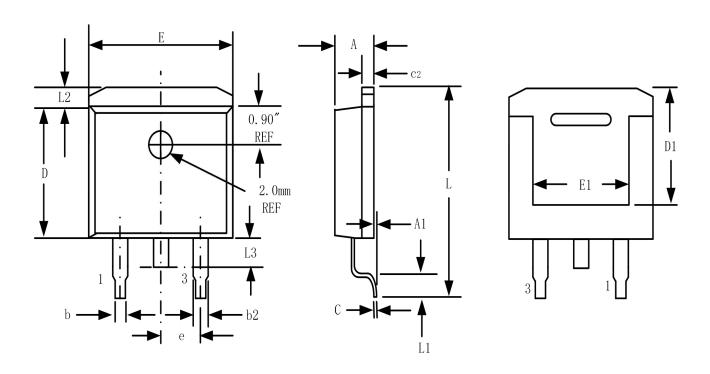
#### 3) Unclamped Inductive Switching Test Circuit & Waveforms







# **TO-263-3L Package Information**

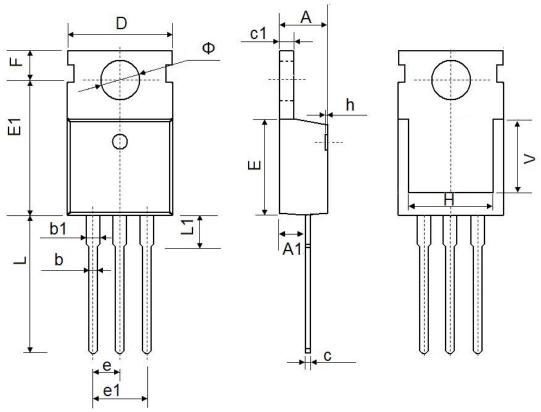


| Symbol | Dimensions | In Millimeters | Dimensions In Inches |       |  |
|--------|------------|----------------|----------------------|-------|--|
| Symbol | Min.       | Max.           | Min.                 | Max.  |  |
| А      | 4.32       | 4.57           | 0.170                | 0.180 |  |
| A1     | -          | 0.25           |                      | 0.010 |  |
| b      | 0.71       | 0.94           | 0.028                | 0.037 |  |
| b2     | 1.15       | 1.40           | 0.045                | 0.055 |  |
| С      | 0.46       | 0.61           | 0.018                | 0.024 |  |
| c2     | 1.22       | 1.40           | 0.048                | 0.055 |  |
| D      | 8.89       | 9.40           | 0.350                | 0.370 |  |
| D1     | 8.01       | 8.23           | 0.315                | 0.324 |  |
| E      | 10.04      | 10.28          | 0.395                | 0.405 |  |
| E1     | 7.88       | 8.08           | 0.310                | 0.318 |  |
| е      | 2.54       | 2.54 BSC       |                      | BSC   |  |
| L      | 14.73      | 15.75          | 0.580                | 0.620 |  |
| L1     | 2.29       | 2.79           | 0.090                | 0.110 |  |
| L2     | 1.15       | 1.39           | 0.045                | 0.055 |  |
| L3     | 1.27       | 1.77           | 0.050                | 0.070 |  |

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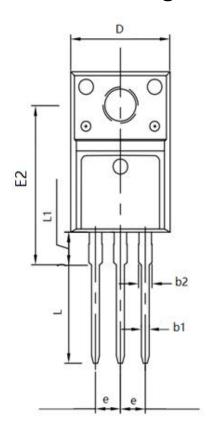
# **TO-220-3L-C Package Information**

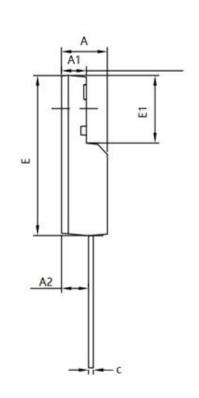


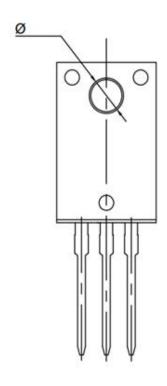
| Ob-al  | Dimensions I | In Millimeters | Dimensions In Inches |       |  |
|--------|--------------|----------------|----------------------|-------|--|
| Symbol | Min.         | Max.           | Min.                 | Max.  |  |
| Α      | 4.400        | 4.600          | 0.173                | 0.181 |  |
| A1     | 2.250        | 2.550          | 0.089                | 0.100 |  |
| b      | 0.710        | 0.910          | 0.028                | 0.036 |  |
| b1     | 1.170        | 1.370          | 0.046                | 0.054 |  |
| С      | 0.330        | 0.650          | 0.013                | 0.026 |  |
| c1     | 1.200        | 1.400          | 0.047                | 0.055 |  |
| D      | 9.910        | 10.250         | 0.390                | 0.404 |  |
| E      | 8.9500       | 9.750          | 0.352                | 0.384 |  |
| E1     | 12.650       | 12.950         | 0.498                | 0.510 |  |
| е      | e 2.540 TYP. |                | 0.100                | TYP.  |  |
| e1     | 4.980        | 5.180          | 0.196                | 0.204 |  |
| F      | 2.650        | 2.950          | 0.104                | 0.116 |  |
| Н      | 7.900        | 8.100          | 0.311                | 0.319 |  |
| h      | 0.000        | 0.300          | 0.000                | 0.012 |  |
| L      | 12.900       | 13.400         | 0.508                | 0.528 |  |
| L1     | 2.850        | 3.250          | 0.112                | 0.128 |  |
| V      | 7.500        | REF.           | 0.295                | REF.  |  |
| Ф      | 3.400        | 3.800          | 0.134                | 0.150 |  |



# **TO-220F Package Information**







| Symbol | Dimensions | In Millimeters | Dimensions In Inches |       |  |
|--------|------------|----------------|----------------------|-------|--|
|        | Min.       | Max.           | Min.                 | Max.  |  |
| А      | 4.500      | 4.900          | 0.177                | 0.193 |  |
| A1     | 2.340      | 2.740          | 0.092                | 0.108 |  |
| A2     | 2.560      | 2.960          | 0.101                | 0.117 |  |
| b1     | 0.700      | 0.900          | 0.028                | 0.035 |  |
| b2     | 1.180      | 1.580          | 0.046                | 0.062 |  |
| С      | 0.400      | 0.600          | 0.016                | 0.024 |  |
| D      | 9.960      | 10.360         | 0.392                | 0.408 |  |
| E      | 15.670     | 15.970         | 0.617                | 0.629 |  |
| E1     | 6.500      | 6.900          | 0.256                | 0.272 |  |
| E2     | 15.500     | 16.100         | 0.610                | 0.634 |  |
| е      | 2.540      | ) TYP          | 0.100                | ) TYP |  |
| Ф      | 3.080      | 3.280          | 0.121                | 0.129 |  |
| L      | 12.640     | 13.240         | 0.498                | 0.521 |  |
| L1     | 3.030      | 3.430          | 0.119                | 0.135 |  |



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